

IN THE CLAIMS:

1. (Currently amended) An electron beam aligner comprising:
a substrate holder provided within an exposure chamber, [[and for holding]] which holds a substrate on which surface a resist film is formed; and
electron beam irradiation means for irradiating said resist film with an electron beam;
and
~~gas collection means provided on said exposure chamber by directly connecting thereto, and for collecting an outgassing released from said resist film when irradiated with said electron beam, wherein~~
said exposure chamber is arranged such that an outgas released from said resist film is trapped when irradiated with said electron beam.

2. (Original) The electron beam aligner of Claim 1, further comprising gas analysis means for analyzing a constituent of said outgassing collected by said gas collection means.

3. (Currently amended) An electron beam aligner comprising:
a substrate holder provided within an exposure chamber, [[and for holding]] which holds a substrate on which surface a resist film is formed;
electron beam irradiation means for irradiating said resist film with an electron beam;
and
~~gas analysis means provided on said exposure chamber by directly connecting thereto, and for analyzing a constituent of an outgassing released from said resist film when irradiated with said electron beam. wherein~~
said exposure chamber is arranged such that an outgas released from said resist film is analyzed when irradiated with said electron beam.

4. (Previously presented) An outgassing collection method comprising the steps of:
holding, within an exposure chamber, a substrate on which surface a resist film is formed;
irradiating said resist film with an electron beam; and
collecting an outgassing released from said resist film when irradiated with said electron beam.

5. (Previously presented) An outgassing analysis method comprising the steps of:
holding, within an exposure chamber, a substrate on which surface a resist film is formed;
irradiating said resist film with an electron beam;
collecting an outgassing released from said resist film when irradiated with said electron beam; and
analyzing a constituent of said collected outgassing.

6. (Previously presented) An outgassing analysis method comprising the steps of:
holding, within an exposure chamber, a substrate on which surface a resist film is formed;
irradiating said resist film with an electron beam; and
analyzing a constituent of an outgassing released from said resist film when irradiated with said electron beam.

7. (New) An outgas collection method comprising the steps of:
holding, within an exposure chamber, a substrate on which surface a resist film is
formed;
irradiating said resist film with an electron beam; and
collecting an outgas released from said resist film by irradiating with said electron
beam.